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Switching Properties of TI2GalnSe4 Single Crystal

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Abstract

Investigation of the switching phenomenon on TI2GalnSe4 single crystal, revealed that it is typical for a memory switch. The switching process takes place with both polarities on the crystal and have symmetrical shapes. Current-voltage characteristics (CVC) of symmetrical Ag/TI2GalnSe(4)/Ag structures exhibit two distinct regions, high resistance "off" state and low resistance "on" state having negative differential resistance (NDR). TI2GalnSe4 is a quaternary semiconductor exhibiting S-type I-V characteristics. The experimental results indicate that the phenomenon in our sample is very sensitive to temperature, light intensity and sample thickness. The switching parameters were checked under the influence of different factors of the ambient conditions. The present study is the first for this phenomenon in TI2GalnSe4 compound.

Keywords

Author Keywords: [Memory](#); [Switching](#); [Effect-Quaternary](#); [Compound-S](#); [Shape-NDR](#); [Region](#)

KeyWords Plus: [TRANSPORT-PROPERTIES](#); [THIN-FILMS](#); [GLASSES](#); [MEMORY](#); [SEMICONDUCTOR](#); [TL2GAINSE4](#); [TLGATE2](#); [DEPENDENCE](#); [BEHAVIOR](#)

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